

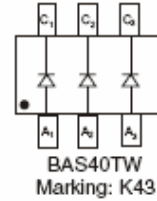
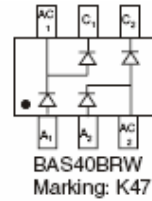
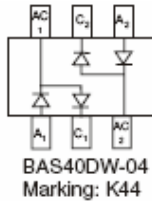
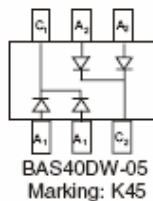
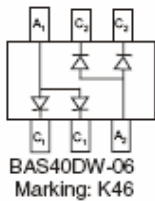
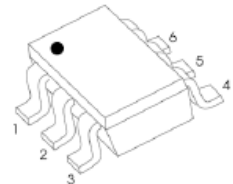
Plastic-Encapsulate Transistors

SCHOTTKY BARRIER DIODE ARRAYS

FEATURES

- Low Forward voltage drop
- Fast switching

SOT-363



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	40	V
DC Blocking Voltage	V_R		
Average Rectified Output Current	I_O	200	mA
Power Dissipation	P_d	200	mW
Thermal Resistance. Junction to Ambient Air	$R_{\theta JA}$	625	°C/W
Junction temperature	T_J	125	°C
Storage temperature range	T_{STG}	-65-125	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 10\mu A$	40		V
Reverse voltage leakage current	I_R	$V_R = 30V$		200	nA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 40mA$		380 1000	mV
Total capacitance	C_T	$V_R = 0, f = 1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F = 10mA, I_R = I_F = 1mA$ $R_L = 100\Omega$		5	ns



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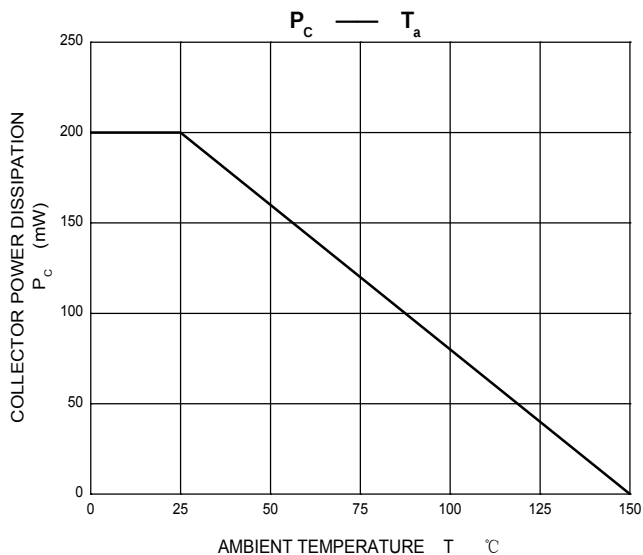
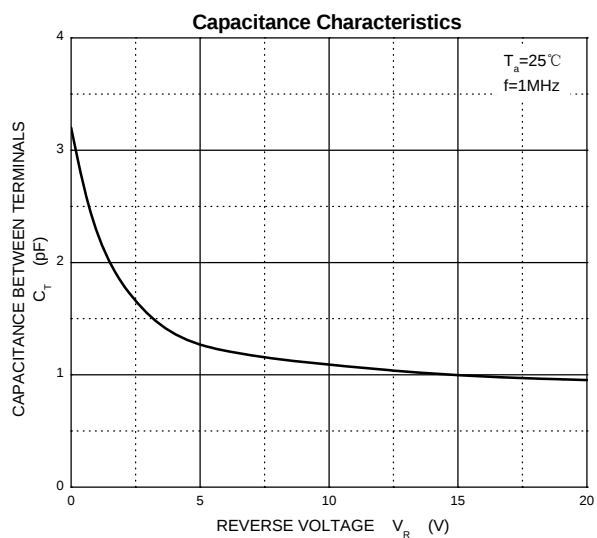
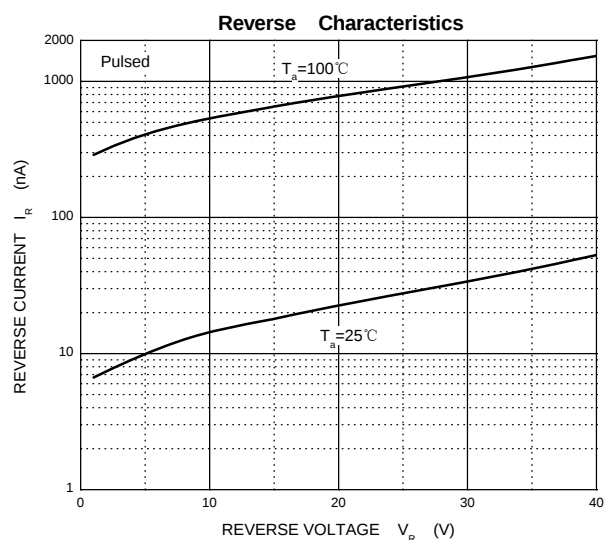
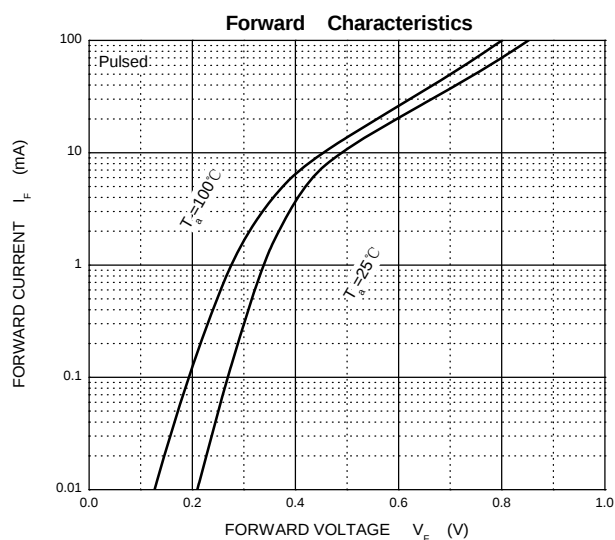
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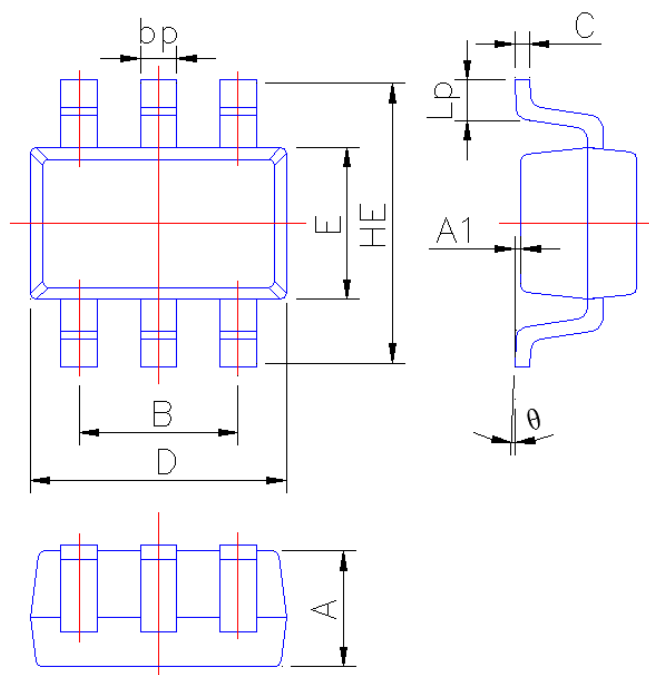
BAS40TW/DW-04/DW-05/DW-06/BRW

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Typical Characteristics



SOT-363 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°